

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1 and (wire\$6 or connect\$6) same switch\$6 same device and (wire\$6 or connect\$6) same pixel\$1 same electrode\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:04
		("257"/\$.ccls.) and ((magnetoresistive and random adj access adj memory) or MRAM) and and (driv\$6 and circuit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 22:32
L1	9	MEMORY SAME CIRCUIT\$6 and coupl\$6 same flip-flop and two same (magnetoresistive and random adj access adj memory or MRAM)and word	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:16
L2	6	MEMORY SAME CIRCUIT\$6 and coupl\$6 same flip-flop and two same (magnetoresistive and random adj access adj memory or MRAM) and word and mask\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 17:16
L3	2	"6188615".pn. and switch\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:15
L4	0	"6188615".pn. and switch\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:16
L5	0	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and swtich\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:17
L6	0	MEMORY SAME CIRCUIT\$6 and (magnetoresistive and random adj access adj memory or MRAM) and swtich\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:17
L7	29	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and switch\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:18

EAST Search History

L8	23	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and switch\$6 and pixel\$1 and bit\$1 same line and word\$6 same line\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:22
L9	8	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and switch\$6 and pixel\$1 and bit\$1 same line and connect\$6 same different same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:24
L10	9	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and switch\$6 and pixel\$1 and bit\$1 same line and connect\$6 same (different or opposit\$6) same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:25
L11	23	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and switch\$6 and pixel\$1 and bit\$1 same line and connect\$6 and (different or opposit\$6) same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:46
L12	1045	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 same line and connect\$6 and (different or opposit\$6) same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:02
L13	321	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 same line and connect\$6 same (different or opposit\$6) same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:35
L14	191	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 same line same connect\$6 same (different or opposit\$6) same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:35
L15	165	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 adj line same connect\$6 same (different or opposit\$6) same direct\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:36
L16	1	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 adj line same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6 same over	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:36

EAST Search History

L17	1	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 same line same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6 same over	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:37
L18	38	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 same line same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:37
L19	37	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and bit\$1 adj line same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:37
L20	36	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (bit\$1 adj line\$1) same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6 and (word\$6 adj Line\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:45
L21	16	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (bit\$1 adj line\$1) same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6 and (word\$6 adj Line\$1) and mask\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 19:41
L22	2	"6697294".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:10
L23	0	"6697294".pn. and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:10
L25	1	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (bit\$1 adj line\$1) same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6 and (word\$6 adj Line\$1) and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:19

EAST Search History

L26	2	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (bit\$1 adj line\$1) same connect\$6 same (different or opposit\$6) same direct\$6 same cross\$6 and (word\$6 adj Line\$1) and flip-flop\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:45
L27	13	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and switch\$6 and pixel\$1 and bit\$1 same line and connect\$6 and (different or opposit\$6) same direct\$6 and flip-flop\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 20:47
L28	3	"20030012279"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 22:54
L29	2	"20030122790"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 22:54
L30	0	"20030122790" and mask\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 22:54
L31	66	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:03
L32	29	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and pixel\$1 and switch\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:03
L33	5	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and pixel\$1 and switch\$6 and mask\$6 same layer\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:05
L34	456	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and mask\$6 same layer\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:05

EAST Search History

L35	96	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and mask\$6 adj layer\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:05
L36	0	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (mask\$6 adj layer\$6) same gate same word\$6 same Line\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:06
L37	28	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (mask\$6) same gate same word\$6 same Line\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:10
L38	8	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (mask\$6) same gate same word\$6 same Line\$1 and bit same line and column same line same mask\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:11
L39	15	MEMORY SAME CIRCUIT\$6 and two same (magnetoresistive and random adj access adj memory or MRAM) and (mask\$6) same gate same word\$6 same Line\$1 and bit same line same mask\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:12
L40	0	plasma adj panel adj display and light adj absorbing adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:57
L41	0	plasma adj panel adj display and light\$6 adj absorb\$6 adj layer\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:58
L42	4	plasma adj panel adj display and light\$6 same absorb\$6 same layer\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 23:58
S1	0	MEMORY SAME CIRCUIT\$6 and manetresissive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 15:54

EAST Search History

S2	3073	MEMORY SAME CIRCUIT\$6 and magnetoresistive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 15:54
S3	4568	MEMORY SAME CIRCUIT\$6 and (magnetoresistive adj random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 15:55
S5	30	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 16:06
S6	22	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 16:03
S7	9	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:24
S8	6	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6 and pixel\$1 and electrode\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 15:58
S9	2	"5,307,169".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/09 16:00
S10	31	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and (magnetoresistive adj random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:23
S11	31	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and ((magnetoresistive same random same access same memory) or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:23

EAST Search History

S12	32	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and (magnetoresistive and random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 09:02
S13	62	MEMORY SAME CIRCUIT\$6 and coupl\$6 same flip-flop and (magnetoresistive and random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:24
S15	9	(MEMORY SAME CIRCUIT\$6 and coupl\$6 same flip-flop) and (magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:25
S16	9	(MEMORY and CIRCUIT\$6 and coupl\$6 same flip-flop) and (magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:25
S17	9	(MEMORY and CIRCUIT\$6 and coupl\$6 and flip-flop) and (magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:26
S18	52	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:26
S19	9	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6 and coupl\$6 and flip-flop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:46
S20	9	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6 and flip-flop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:27
S22	18	(MEMORY SAME CIRCUIT\$6 and coupl\$6 and (flip-flop or latch)) and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:45
S23	1	"20060245263" and (magnetoresistive adj random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:31

EAST Search History

S24	9	(MEMORY SAME CIRCUIT\$6 same coupl\$6 and (flip-flop or latch)) and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:46
S25	11	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6 and coupl\$6 and (flip-flop\$6 or latch\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:52
S26	45	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:00
S27	8	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6 and "345"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 12:52
S28	436106	("345"/\$.ccls. or "257"/\$.ccls.)(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:01
S29	45	(magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:00
S30	12	("345"/\$.ccls. or "257"/\$.ccls.) and (magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 14:10
S31	36	("257"/\$.ccls.) and (magnetoresistive and random adj access adj memory) and input\$6 and display\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:11
S32	6	("257"/\$.ccls.) and (magnetoresistive and random adj access adj memory) and input\$6 and display\$6 and pixel\$1 and CIRCUIT\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:09
S33	1460	("257"/\$.ccls.) and ((magnetoresistive and random adj access adj memory) or MRAM) and (driv\$6 ands circuit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:13

EAST Search History

S34	699	("257"/\$.ccls.) and ((magnetoresistive and random adj access adj memory) or MRAM) and (driv\$6 and circuit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:13
S35	380	("257"/\$.ccls.) and ((magnetoresistive and random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:13
S36	350	("257"/\$.ccls.) and ((magnetoresistive adj random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:14
S37	241	("257"/\$.ccls.) and ((magnetoresistive adj random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6) and couple\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:14
S38	5	("257"/\$.ccls.) and ((magnetoresistive adj random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6) and couple\$6 same flip-flop\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:17
S39	3	("257"/\$.ccls.) and ((magnetoresistive adj random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6) and couple\$6 same flip-flop\$6 and (video\$6 or display\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:17
S40	15	("257"/\$.ccls.) and ((magnetoresistive adj random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6) and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:22
S41	12	("257"/\$.ccls.) and ((magnetoresistive adj random adj access adj memory) or MRAM) and (driv\$6 same circuit\$6) and pixel\$1 and input\$6 and (display\$6 or video same image\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:18
S42	1	"20060216877" and ((magnetoresistive adj random adj access adj memory) or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/10 13:20
S43	0	"6538921".pn. and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 11:57

EAST Search History

S44	0	"6538921".pn. and video	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 11:58
S45	0	"6538921".pn. and display	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 12:27
S46	9	(MEMORY SAME CIRCUIT\$6 and coupl\$6 same flip-flop) and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 12:00
S47	1	"6538921".pn. and bit and line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 12:34
S48	1	"6538921".pn. and word and line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 15:21
S49	0	"6538921".pn. and word and line and address\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 13:04
S51	1	"20060216877" and word and line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 13:14
S52	1	"20060216877" and word and line and mask\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 14:28
S53	0	"20060216877" and word and line and mask\$6 and address\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 14:28
S54	1	"20060216877" and word and line and mask\$6 and access\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 14:31

EAST Search History

S55	0	"20060216877" and word and line and mask\$6 and access\$6 and (flip-flop\$6 or latch) and clock	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 14:31
S56	0	"20060216877" and word and line and mask\$6 and access\$6 and (flip-flop\$6 or latch) and clock\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 14:32
S57	1	"20060216877" and word and line and mask\$6 and access\$6 and (flip-flop\$6 or latch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 14:32
S58	1	"6538921".pn. and computer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/11 15:21
S59	1731	("257"/\$.ccls.) and ((magnetoresistive and random adj access adj memory) or MRAM) and (driv\$6 ands circuit\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 22:32
S60	14	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:01
S61	0	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1 and wire\$6 same switch\$6 same device same pixel\$1 same electrode\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:02
S62	14	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAM\$1 and bit same line\$1 and bit same line\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:07
S63	0	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1 and wire\$6 same (switch\$6 same device and pixel\$1 same electrode\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:02

EAST Search History

S64	0	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1 and wire\$6 same switch\$6 same device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:03
S65	2	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1 and (wire\$6 or connect\$6) same switch\$6 same device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:03
S66	2	display and switch\$6 same device and pixel\$1 same electrode\$1 and two same MRAMs and bit same line\$1 and bit same line\$1 and (wire\$6 or connect\$6) same switch\$6 same device and (wire\$6 or connect\$6) same pixel\$1 same electrode\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:05
S67	9	(MEMORY SAME CIRCUIT\$6 and coupl\$6 same (flip-flop or latch)) and (magnetoresistive adj random adj access adj memory or MRAM) and input\$6 and display\$6 and pixel\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/27 23:10
S68	11	MEMORY SAME CIRCUIT\$6 same coupl\$6 same flip-flop and two same (magnetoresistive and random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 09:05
S69	13	MEMORY SAME CIRCUIT\$6 and coupl\$6 same flip-flop and two same (magnetoresistive and random adj access adj memory or MRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 17:16
S70	1	"6538921".pn. and word and line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/28 11:31